

# isc N-Channel MOSFET Transistor

# **IXFA130N10T**

#### FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on) ≤ 9.1mΩ@V<sub>GS</sub>=10V
- Fully characterized avalanche voltage and current
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATION

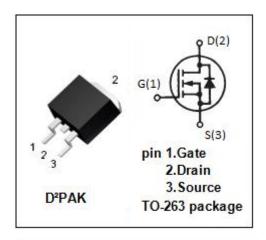
- DC/DC Converters
- · High Current Switching Applications

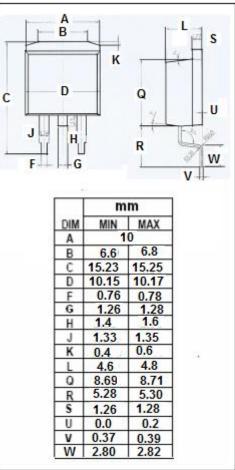
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                                  | VALUE   | UNIT       |  |
|------------------|--|---------|------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                       | 100     | V          |  |
| V <sub>GS</sub>  | Gate-Source Voltage                        | ±30     | V          |  |
| I <sub>D</sub>   | Drain Current-Continuous                   | 130     | А          |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed 350            |         | А          |  |
| P <sub>D</sub>   | Total Dissipation @T <sub>C</sub> =25℃ 360 |         | W          |  |
| Tj               | Operating Junction Temperature             | -55~175 | $^{\circ}$ |  |
| T <sub>stg</sub> | Storage Temperature                        | -55~175 | $^{\circ}$ |  |

### • THERMAL CHARACTERISTICS

| SYMBOL               | PARAMETER                           | MAX  | UNIT |
|----------------------|-------------------------------------|------|------|
| R <sub>th(j-c)</sub> | Junction-to-case thermal resistance | 0.42 | °C/W |







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | MAX  | UNIT |
|---------------------|--------------------------------|--|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> = 0V; ID = 250 μ A   | 100 |      | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> = V <sub>GS</sub> ; ID = 1mA                                     | 2.5 | 4.5  | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> = 25A                                       |     | 9.1  | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V                                       |     | ±200 | nA   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V                        |     | 10   | - μΑ |
|                     |                                | V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 150°C |     | 500  |      |
| V <sub>SD</sub>     | Diode forward voltage          | I <sub>F</sub> = 25A; V <sub>GS</sub> = 0V                                       |     | 1.0  | V    |

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